

# Photoconductivity of CdS-CdSe granular films: influence of microstructure

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We study experimentally the photoconductivity of CdS-CdSe sintered granular films obtained by the screen printing method. We mostly focus on the dependences of photoconductivity on film's microstructure, which varies with changing heat-treatment conditions. The maximum photoconductivity is found for samples with compact packing of individual grains, which nevertheless are separated by gaps. Such a microstructure is typical for films heat-treated during an intermediate (optimal) time. In order to understand whether the dominant mechanism of charge transfer is identical with the one in monocrystals, we perform temperature measurements of photoresistance. Corresponding curves have the same peculiar nonmonotonic shape as in CdSe monocrystals, from which we conclude that the basic mechanism is also the same. It is suggested that the optimal heat-treatment time appears as a result of a competition between two mechanisms: improvement of film's connectivity and its oxidation. Photoresistance is also measured in vacuum and in helium atmosphere, which suppress oxygen and water absorption/chemisorption at intergrain boundaries. We demonstrate that this suppression increases photoconductivity, especially at high temperatures.

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## I. INTRODUCTION

Materials with granular structure are widely used in modern electronics and radio engineering. These materials can be fabricated either by the traditional screen printing method known for a long time or by using new technologies, such as the direct forming of electronic devices by printers and opal crystals creation by concretion of spherical microparticles from water dredges. Modern technologies enable one to fabricate much more pure and reproducible samples compared to the old ones. As a rule, by using these methods materials with granular or polycrystalline internal structure are obtained. In general, it is not always clear a priori how granularity affects various electrophysical characteristics of a material[1]. Therefore, electronic and optical properties of granular semiconductors attract a lot of attention now.

Films made of CdS and CdSe are familiar due to the high photoconductivity and photosensitivity they demonstrate. Photoresistors based on these materials are widely used in applications as photodetectors and optical couplers [2, 3, 4, 5]. The investigations of photoconductive CdSe and CdS systems have a long history, see e.g. Refs. [6, 7]. It was realized long time ago that a model with the single type of recombination centers cannot account for various electronic properties of CdSe and CdS crystals, such as superlinearity of photoconductivity, infrared and thermal quenching [7]. Instead a picture based on two types of states in the forbidden gap was proposed [7] (see also Ref. [8], where even two more kinds of centers were introduced). It was found[6, 7, 9] that photosensitivity of CdSe monocrystals can be as high as  $10^6 - 10^8$ . Granular structure of thin films made of CdSe or CdS makes the physics of these systems even

more complicated[1, 6, 10, 11, 12] due to possible formation of space charged regions inside individual crystallites and at boundaries.

In the recent paper[13] some of us studied the influence of heat-treatment conditions for  $\text{CdS}_{1-x}\text{Se}_x$  granular films, obtained by the screen printing method, on their photoconductivity. It was found that there is some optimal time for sample's heat-treatment with the quasi-free air access (at fixed temperature of heat-treatment), for which the photoconductivity is maximized. The light-to-dark current ratio for these films can be as large as  $10^9$ . This fact, together with the simple and low-cost method of film's fabrication, make them quite perspective for technological applications. The characteristic feature of optimally-prepared films is that neighboring grains, from which they are build, fit each other on large contact areas. At the same time, long time of heat-treatment results in the recrystallization of grains and disappearance of spaces between them, so that the film's connectivity is significantly improved compared to optimally-prepared films. From these studies, it has remained unclear whether the leading mechanism of charge transfer under the illumination is associated with intergrain boundaries or it is identical with that for monocrystals of the same chemical composition. It is also not evident why almost total disappearance of gaps between grains is accompanied by the decrease of photoconductivity, while it is expectable that gaps prevent grain-to-grain charge transfer. The main goal of the present paper is to understand if the leading mechanism of charge transfer in these films is different from the one in crystals. For simplicity, we here restrict ourselves on  $\text{CdS}_{0.2}\text{Se}_{0.8}$  films only. In addition to the visual analysis of SEM images of film's microstructure, we perform AFM studies of intergrain boundaries. We also measure temperature dependences of photoresistance and compare the character of these quite nontrivial dependences with the ones for monocrystals, which are known from literature. Additionally, we perform measurements in vacuum, as well as in the atmosphere of helium, which suppresses oxygen and water absorption/chemisorption at grain boundaries, and compare the obtained results with the ones for the atmosphere of air. These measurements indicate that surfaces indeed play some role in the charge transfer under the illumination, since absorbed oxygen and water decrease photoconductivity. We finally make a conclusion that the leading mechanism of charge transfer in the systems studied is most probably the same as in monocrystals, while the existence of the optimal heat-treatment time is due to the competition between the oxidation of grain boundaries during their heat-treatment, which suppresses charge transfer, and improvement of film's connectivity, which facilitates this process.

The paper is organized as follows. Section II deals with the sample characterization. In Section III, we describe our experimental setup. In Section IV, we present the results for the measurements of photoresistance and discuss them. We conclude in Section V.

## II. SAMPLE CHARACTERIZATION

We used CdS and CdSe powders as initial components for the paste, from which samples are then fabricated. The initial powders of CdS and CdSe were milled together. The prepared CdS-CdSe powder and the coupler were mixed in a special barrel in order to obtain the paste. Propylene glycol was used as a coupler. Through a stencil, this paste was deposited on the pyroceramics substrate and then seasoned at room temperature for 0.5 hour. After that, samples were dried for 1 hour at the temperature of 373 K in order to remove the coupler. This raw material, represented by a film of 15-20 mkm thickness, was heat-treated in the stove with a quasi-free air access. The time of heat-treatment for different samples varied from 5 to 90 minutes, and the temperature - from 773 K to 873 K. Finally, samples were

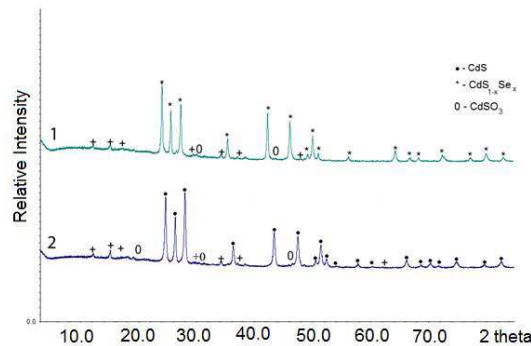


Figure 1: XRD patterns of CdSe-CdS sample (curve 1) and standard CdS sample (curve 2).

washed out in a bidistilled water and dried at room temperature. By using this method, we have prepared more than 50 samples, which were differing from each other by chemical composition, as well as by heat-treatment parameters, i.e., heat-treatment time and temperature. The similar technology of sample fabrication was used by some of us in Ref. [14].

During the heat-treatment process, small particles of the powder corresponding to different chemical compositions, CdS or CdSe, merge into grains, each grain containing large number of initial particles. As we found, these grains consist of a solid CdS-CdSe solution. In order to prove the fact that the solid solution is indeed formed, we performed x-ray analysis of fabricated films. The typical measured XRD patterns for samples are presented in Fig. 1. Positions of narrow peaks on XRD patterns do correspond to the solid solution. The shift in the positions of these peaks depends on the ratio of initial components (CdS and CdSe). Note that a trace quantity of oxide  $\text{CdSO}_3$  was also detected in our samples.

The microstructure of obtained samples was studied by SEM. We found that the microstructure is highly sensitive to the heat-treatment conditions. The analysis of SEM images showed us that heat-treatment increases grains sizes due to their merging. This process is naturally accompanied by the growth of contact areas between neighboring grains and thus to the better fitting between them: grains become more compactly packed. If the heat-treatment time is long enough, samples begin to recrystallize and intergrain boundaries disappear. Typical SEM images for  $\text{CdS}_{0.2}\text{Se}_{0.8}$  films, which were heat-treated at the temperature  $823\text{ K}$ , are presented in Fig. 2. Figs. 2(a), (b), and (c) correspond to films which were heat-treated for 5, 30, and 60 minutes, respectively. We found that the average grain size was around  $3\text{-}12\ \mu\text{m}$  in all these cases with the tendency of this size to increase upon the prolongation of the heat-treatment time, as clearly seen from Fig. 2. By its structure, the film in Fig. 2(a) resembles a sand: relatively large spaces exist between neighboring grains, these grains being connected to each other only by rather small areas on their surfaces due to the rounded shape of grains. At the same time, spacings between grains on Fig. 2(c) seem to disappear, many of them now reduce to grooves. Fig. 2(b) corresponds to the intermediate heat-treatment time, which leads to a compact packing of grains; nevertheless narrow, long and deep gaps between them still exist. Images of higher resolution, compared to the ones, presented here, support these conclusions.

In order to study in a more detail the structure and geometry of boundaries between grains, we used a semicontact AFM with a thin cantilevers of whisker type. The typical radius of curvature for the whisker was  $10\text{ nm}$  and the typical height was  $1\ \mu\text{m}$ . Figs. 3 (a) and (b) show the AFM images for the structure and profiles of typical grain boundaries

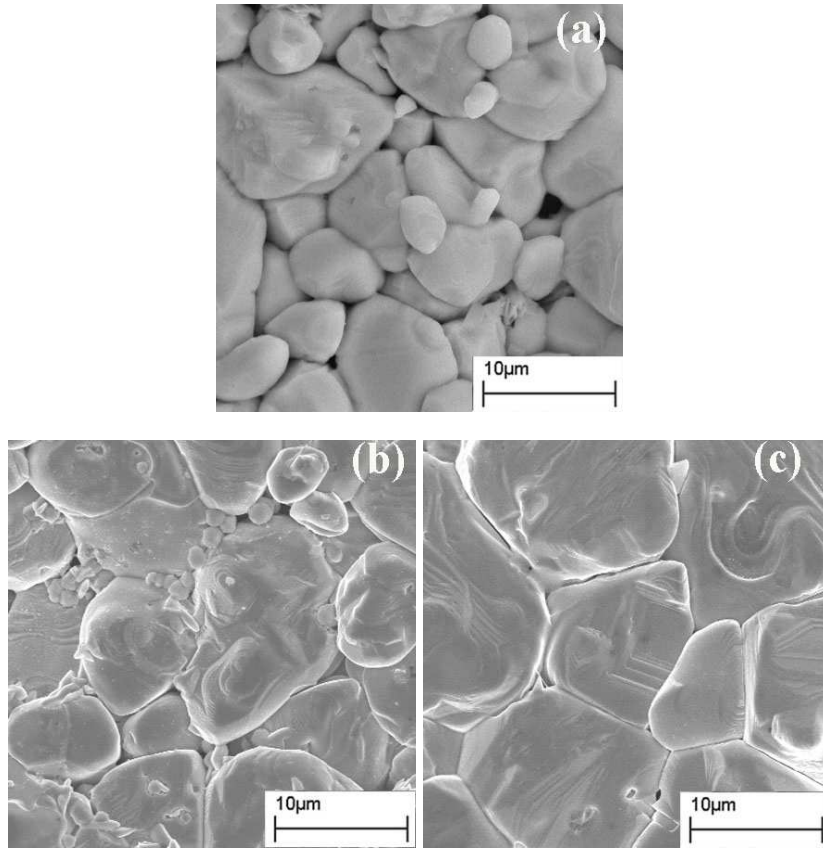


Figure 2: Micrographs of granular  $\text{CdS}_{0.8}\text{Se}_{0.2}$  films fabricated with different times of heat-treatment at fixed temperature 823 K: 5 minutes (a), 30 minutes (b), 60 minutes (c).

in samples, which were previously studied by SEM and which were fabricated during the 30 and 60 minutes of heat-treatment, respectively. The micro-relief of samples, obtained by 5 minutes of heat-treatment, can not be investigated using this experimental approach, since the surface landscape is very nonuniform in this case, which prevents the use of a whisker. It is seen from Fig. 3 that our expectations, obtained from the visual analysis of SEM images, are basically correct: samples, which were sintered during an intermediate time, contain narrow gaps, which do not disappear completely during the fabrication process. These gaps become more and more narrow when moving away from the film surface towards its interior regions. Spacings between grains in films, which were heat-treated for a long time, tend to disappear and they shrink into grooves on the film surface, see Fig. 3(b), which shows such a groove separating two regions of the grain with different growth orientations.

### III. EXPERIMENTAL SETUP

The experimental setup allowed us to study film's specific resistance by spreading resistance method. For measurements of the resistance, we used indium contacts, which were prepared by the transfer of melted indium from Teflon plate under the pressure applied. The obtained contacts have a square shape with one millimeter on side. The distance between contacts is also one millimeter. Samples were placed in an isolated chamber that allows to study

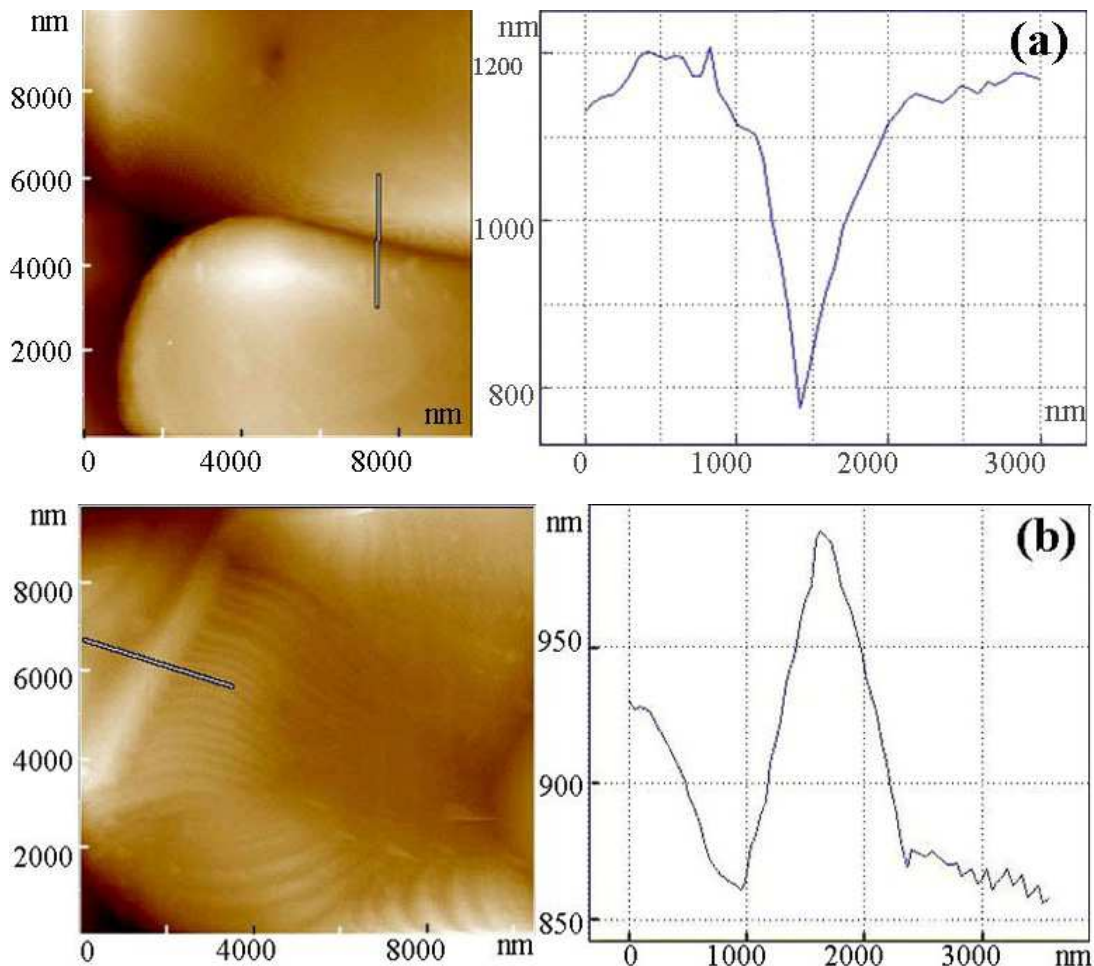


Figure 3: AFM images of intergrain boundaries for the sample, heat-treated for 30 minutes (a) and for 60 minutes (b). Right panels show the images themselves, left panels give the profiles of landscapes along the lines marked by short lines in right panels.

the influence of various gaseous atmospheres (at pressures close to the atmospheric pressure) and of vacuum. It was also possible to use streams of gases for the same purposes. An incandescent lamp served as a source of light. By changing the distance between the lamp and the film, we tuned the intensity of light, which illuminated the samples. The film's resistance was measured under the illumination up to  $10^4$  lux and at the temperature varying from room temperature to 420 K.

#### IV. RESULTS AND DISCUSSION

As it was shown in Ref. [13], the highest photoconductivity at room temperature was achieved for films, which were heat-treated during an intermediate time, nearly 30 minutes, at heat-treatment temperature 823 K. Here we focus on temperature dependences of photoresistance  $R(T)$  for samples characterized by different heat-treatment parameters. We expect that these dependences can shed a light on the leading mechanism of charge transfer. In total, for  $R(T)$  measurements we used more than 30 samples, and the results were reproducible. Fig. 4 gives typical temperature

dependences for the fixed illumination of 100 lux. It is clearly seen from this figure that the shape of all these curves is rather peculiar: they consist of two segments demonstrating opposite tendencies. At low temperatures, resistance grows with the increase of temperature, while at high temperatures it decreases. The first type of behavior is quite unusual for conventional semiconductors and isolators (and common for metals), where charge transfer occurs by the simple thermal activation of carriers through the forbidden gap. However, similar temperature dependences of photoresistance are found in CdSe monocrystals[6] with the "anomalous" part of  $R(T)$  curve being localized in nearly the same range of temperatures. The non-monotonic behavior is explained by the presence of two different types of centers in the forbidden gap[6]. Note also that CdSe crystals demonstrate very high light-to-dark current ratio[6], which is comparable to the the one of samples studied here[13]. Since quite peculiar temperature dependence of photoresistance found in our granular films is similar to that in monocrystals, it is reasonable to suggest that the leading mechanism of charge transfer under an illumination is unique both in our samples and in monocrystals, while the influence of internal boundaries is a less important factor. This factor, however, is not negligible because it can provide an additional increase of photoconductivity up to one order of magnitude in certain range of temperatures by varying annealing conditions, as seen from Fig. 4 (compare, for instance, curves 1 and 3 near the temperature of 100 C). It is also worth noticing that the optimal heat-treatment time, which maximizes the photoconductivity, is strongly dependent on the temperature at which the photoconductivity is tested. While this optimal time was found to be approximately 30 minutes for room temperature, it shifts towards 1 hour when temperature is rising up to 160 C. Surprisingly, at lower temperatures, the resistance of the film heat-treated for 5 minutes (curve 1) is significantly lower than that for the sample, heat-treated for 60 minutes (curve 3), although the connectivity of the first sample is much more poor compared to the second one. In general, heat-treatment with the (quasi)-free air access is associated with two factors: (i) it leads to the improvement of contacts between individual grains and moreover to the merging of grains, (ii) it also results in the oxidation of boundaries. The first factor naturally leads to the decrease of photoresistance in a dominant (bulk) channel. The second factor leads to the increase of photoresistance. Therefore, an optimal heat-treatment time can appear as a result of the competition between the two factors. For our films, second factor is not negligible at all, as a comparison between curves 1 and 3 in Fig. 4 implies. Notice that the existence of annealing temperatures, which maximize photosensitivity, was reported in Ref. [15] for CdSe thin films obtained by a chemical bath deposition technique.

In order to better understand the role of oxygen and water, which are absorbed/chemisorbed at the surfaces, we performed experimental investigations of photoresistance in helium atmosphere, in vacuum, and also in the stream of helium, after keeping samples in these environment for 1 hour. These conditions diminish oxygen and water absorption at intergrain boundaries, as well as at the film's surface. Of course, an oxide layer cannot be removed by this method, since this layer essentially appears during the heat-treatment with a quasi-free air access. Fig. 5 presents the typical results for  $R(T)$  dependence at constant illumination of 1500 lux in the atmosphere of air, helium, and in the vacuum for the samples heat-treated for 30 minutes. Firstly, shape of all these curves is not dependent on the atmosphere, which evidences that non-monotonic  $R(T)$  dependence cannot be due to oxidation/deoxidation processes during sample's heating/cooling: This is consistent with the suggested idea that the dominant mechanism of charge transfer is the same as in monocrystals. Secondly, it is seen from Fig. 5 that the lowest photoresistance is achieved in the vacuum, i.e., when oxygen and water absorption is suppressed, while the highest photoresistance shows up in the air atmosphere. The influence of absorption is not very strong at low temperatures, i.e., at the "anomalous" parts

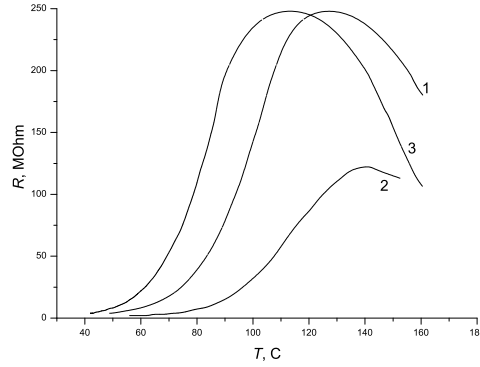


Figure 4: Temperature dependences of film's photoresistance at fixed illumination of 100 lux for samples with different times of heat-treatment during their fabrication: 5 minutes (curve 1), 30 minutes (curve 2), 60 minutes (curve 3).

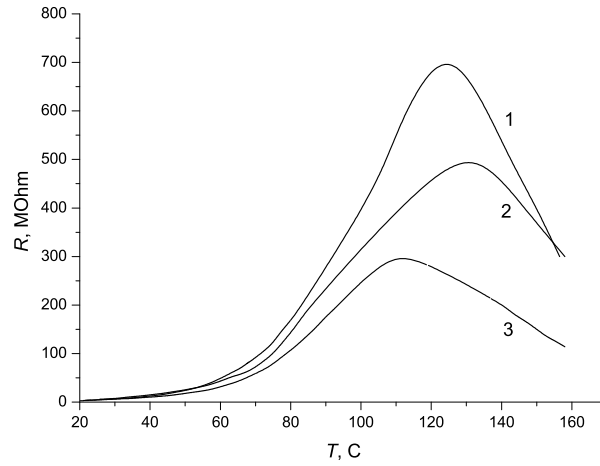


Figure 5: Temperature dependences of film's photoresistance at fixed illumination of 1500 lux in different environments: in air (curve 1), in helium (curve 2), in vacuum (curve 3).

of  $R(T)$  curves, since their absolute values of photoresistance for different curves vary only within 30 %. However, at higher temperatures, when approaching the thermoactivation part of  $R(T)$  curves, an atmosphere starts to play an important role. For instance, the resistance of the sample in vacuum (curve 3) is approximately two times lower than that in the air (curve 1) at  $T = 130$  C. The resistance of the sample in helium atmosphere (curve 2) is lower than that in the air (curve 1), but also higher than the resistance in vacuum (curve 3). This can be attributed to the weaker desorption of air and water in helium environment compared to the vacuum.

We finally notice that different studies of CdS and CdSe films performed in the past provided different results for the temperature dependence of photoresistance. For instance, in Ref. [16], where photoconductivity of  $\text{CdS}_{1-x}\text{Se}_x$  polycrystalline films was investigated, an "anomalous" part of  $R(T)$  curve was not found, the whole dependence being

of "thermoactivation" nature. Ref. [17] deals with CdSSe(Cu) in silicone resin binder layers, which also demonstrates simple monotonic behavior. At the same time, non-monotonic  $R(T)$  dependences, similar to the ones presented here, were reported in Ref. [18] for CdS<sub>1-x</sub>Se<sub>x</sub> sintered layers and in Ref. [19] for CdSe thin films prepared by thermal vacuum evaporation.

## V. CONCLUSIONS

Highly photosensitive granular CdS<sub>0.2</sub>Se<sub>0.8</sub> films were fabricated by the screen printing method. X-ray analysis has shown that grains consist of a solid CdS-CdSe solution. We measured temperature dependences of photoresistance and found that they have a peculiar non-monotonic shape, which is practically identical with that for CdSe monocrystals, known from literature. We therefore conclude that, in these granular films, the leading mechanism of charge transfer under the illumination is the same as in monocrystals, i.e., based on the presence of two kinds of centers in the forbidden gap. Influence of intergrain boundaries is however not negligible. This follows from the fact that photoconductivity also depends on the film's microstructure, which can be changed by tuning the time and temperature of heat-treatment (with the quasi-free air access) during the process of sample's fabrication. The longer heat-treatment time, the larger grains and the more compactly they are packed. The highest photoconductivity at room temperatures was found for films, heat-treated for an intermediate time, in which gaps between grains still exist. This "optimal" heat-treatment time, however, strongly depends on the temperature, at which photoconductivity is probed, namely, it increases with the increase of temperature. For a certain range of temperatures, one can improve photoconductivity as much as up to one order in magnitude by only varying film's internal microstructure. An explanation for the optimal heat-treatment time was suggested in terms of the competition between the two mechanisms: longer heat-treatment improves film's connectivity, but also results in additional oxidation. The optimal heat-treatment time thus appears as a result of the interplay between these two factors. To better understand the effect of grain boundaries, we performed additional measurements of photoresistance in vacuum and also in helium atmosphere, which have shown that oxygen and water absorption/chemisorption at grain boundaries decreases photoconductivity.

## VI. ACKNOWLEDGEMENTS

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